Docket No.: M4065.0239/P239 Micron Ref.: 99-0544.00/US

ABSTRACT

Contact openings in semiconductor substrates are formed through insulative layers using an etchant material. The etchant typically leaves behind a layer of etch residue which interferes with the subsequent deposition of conductive material in the opening, as well as the conductive performance of the resulting contact. A method of etch removal from semiconductor contact openings utilizes ammonia to clean the surfaces thereof of any etch residue.